

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

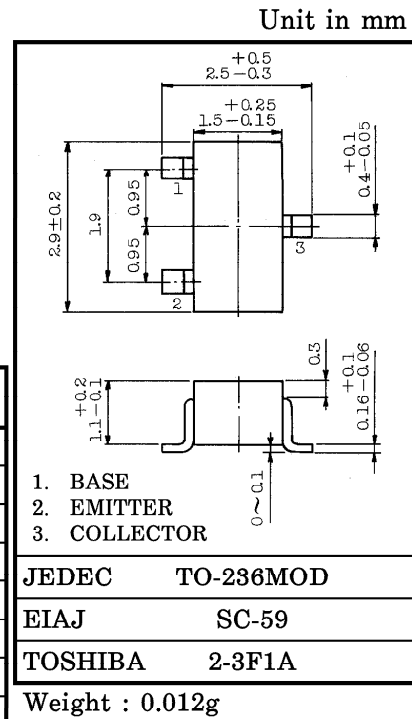
# 2SA1362

LOW FREQUENCY POWER AMPLIFIER APPLICATIONS.  
POWER SWITCHING APPLICATIONS.

- High DC Current Gain :  $h_{FE} = 120 \sim 400$
- Low Saturation Voltage  
:  $V_{CE(sat)} = -0.2V$  (Max.) ( $I_C = -400mA, I_B = -8mA$ )
- Suitable for Driver Stage of Small Motor
- Small Package

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-15	V
Collector-Emitter Voltage	$V_{CEO}$	-15	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-800	mA
Base Current	$I_B$	-160	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

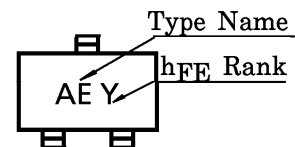


ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -15V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-15	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1V, I_C = -100mA$	120	—	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -400mA, I_B = -8mA$	—	—	-0.2	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -1V, I_C = -10mA$	-0.5	—	-0.8	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	13	—	pF

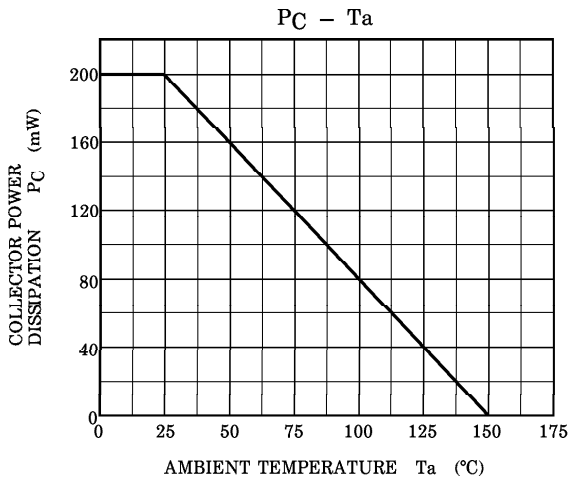
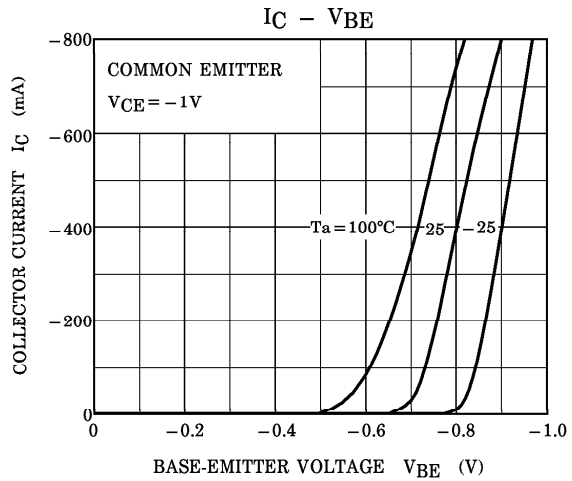
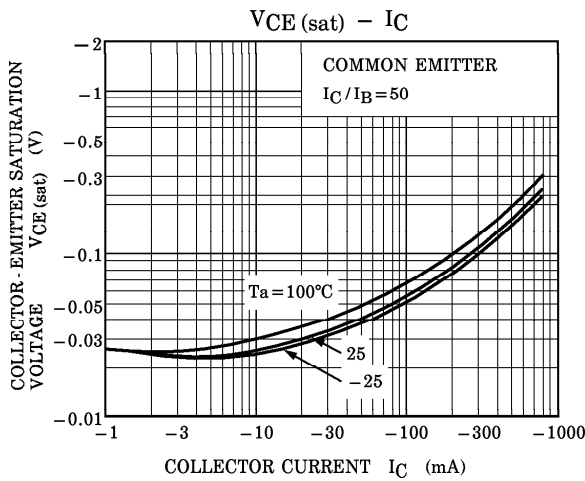
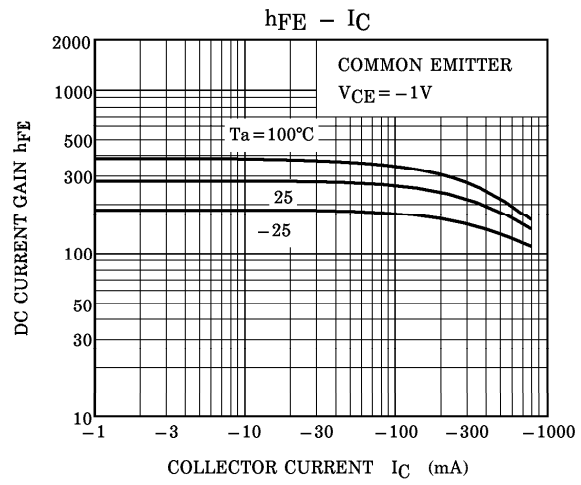
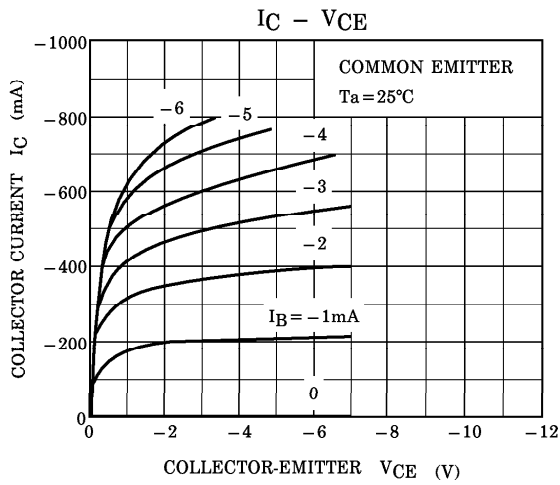
Note :  $h_{FE(1)}$  Classification Y (Y) : 120~240 GR (G) : 200~400  
( ) Marking Symbol

MARKING



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